



#15/Am
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VS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **NIHEI, Mizuhisa et al.**

Group Art Unit: 2815

Serial No.: **09/746,064**

Examiner: **BAUMEISTER, Bradley**

Filed: **December 26, 2000**

P.T.O. Confirmation No.: 1990

For: **SEMICONDUCTOR TRIODE DEVICE HAVING A
COMPOUND-SEMICONDUCTOR CHANNEL LAYER**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

April 11, 2003

Sir:

In response to the Office Action dated **January 14, 2003**, please amend the above-identified application as follows:

IN THE CLAIMS:

ADD new claim 14 to read as follows:

C' 14. (New) A compound semiconductor field effect transistor as claimed in claim 1 wherein said intermediate layer has a thickness of about 4nm.

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